



Bipolar PNP Bare Die – BTP995

Part Description

The BTP995 is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications. NPN complement is BTN995.

Key Parameters:

- VCBO = -500V
- VCEO = -500V
- VEBO = -5V
- hFE = 150-300 @ VCE = -10V, IC = -0.001A
- VCE(Sat) = -0.5V @ IC = -0.5A, IB = -10mA
- fT = 50 MHz @ VCE = -20V, IE = 0A
- COBO = 8pF @ VCB = -20V

Features

Designed to provide performance equivalent to ZETEX / DIODES INC. ZTX56 or NXP / NEXPERIA PBHV9050T

Die Size (Unawn)

850 μ m X 850 μ m, 33 Mils X 33 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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